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Form Approved
OMB No. 0704-0188

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1. REPORT DATE (DD-MM-YYYY) 8-April-2005		2. REPORT TYPE Conference Presentation		3. DATES COVERED (From - To) Jun 2000 - Dec 2005	
4. TITLE AND SUBTITLE Empirical Pseudopotential Modeling of Superlattices				5a. CONTRACT NUMBER	
				5b. GRANT NUMBER	
				5c. PROGRAM ELEMENT NUMBER	
6. AUTHOR(S) A. Ongstad, M. Tilton, G. Dente				5d. PROJECT NUMBER 4866	
				5e. TASK NUMBER LY	
				5f. WORK UNIT NUMBER 12	
7. PERFORMING ORGANIZATION NAME(S) AND ADDRESS(ES)				8. PERFORMING ORGANIZATION REPORT NUMBER	
9. SPONSORING / MONITORING AGENCY NAME(S) AND ADDRESS(ES) AFRL/DELS 3550 Aberdeen Ave SE Kirtland AFB NM 87117-5776				10. SPONSOR/MONITOR'S ACRONYM(S)	
				11. SPONSOR/MONITOR'S REPORT NUMBER(S)	
12. DISTRIBUTION / AVAILABILITY STATEMENT Approved for public release; distribution is unlimited.					
13. SUPPLEMENTARY NOTES Conference Presentation, 28 March 2005, San Francisco, California.					
14. ABSTRACT For several years, we have been accurately calculating the electronic structure of superlattices using a solution technique based on the Empirical Pseudopotential Method (EOM). In our method for forming the superlattice pseudopotential, the critical assumption is that the heterointerface charges are redistributed, making each constituent layer in the superlattice as bulk-like as possible. Here, we demonstrate that our technique for forming the superlattice pseudopotential is fundamentally different from the atomistic pseudopotential approaches that use a superposition of atomic pseudopotentials to represent the superlattice. We then present several applications of our method to InAsGaSb Type-II superlattices and, where possible, we compare our results to those calculated with an effective mass method, as well as to atomistic EPM methods. In all of these comparisons, our method provides excellent agreement with the measured data.					
15. SUBJECT TERMS Empirical Pseudopotential, superlattice, InAs, GaSb, type II interface					
16. SECURITY CLASSIFICATION OF:			17. LIMITATION OF ABSTRACT	18. NUMBER OF PAGES	19a. NAME OF RESPONSIBLE PERSON
a. REPORT Unclassified	b. ABSTRACT Unclassified	c. THIS PAGE Unclassified			Dr. Andrew Ongstad
			Unlimited	10	19b. TELEPHONE NUMBER (include area code) (505) 853-3207

Empirical Pseudopotential Modeling of Superlattices

AS AMENDED
DEO-PA

Gregory C. Dente, Michael Tilton, Andrew Ongstad

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Air Force Research Laboratory

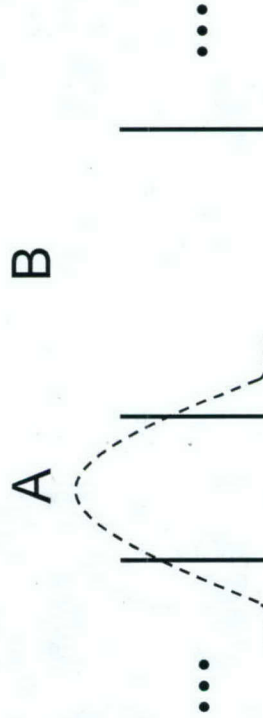
Directed Energy Directorate

“Standard Model”

$\vec{k} \cdot \vec{P}$ perturbation theory

+

Envelope Function Approximation



Clearance is granted for exact content of viewgraphs only.

- We will concentrate on the EPM based models:

$$\left[\frac{-\hbar^2}{2m} \nabla^2 + V(\vec{r}) \right] \Psi = E\Psi$$

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Physics of Bulk Solids with EPM

- Constructing the bulk potential:

$$V(\vec{r}) = \dots + \dots + \dots + \dots$$

$$V(\vec{r}) = \sum_{\vec{r}} \Omega_{lattice}(\vec{r} + \vec{t})_{site} = \sum_{\vec{g}} V_{\vec{g}} e^{i\vec{g} \cdot \vec{r}} = \sum_{\vec{g}} V_{\vec{g}} \alpha \tilde{\Omega}(\vec{k}) \Big|_{\vec{k} = \vec{g}} = \text{form factor}$$

in which $\{\vec{g}\}$ are the reciprocal lattice vectors such that $\vec{g} \cdot \vec{r} = \text{Integer} \cdot 2\pi$.

This forces:

$$V(\vec{r}) = V(\vec{r} + \vec{t})$$

$$\left(\frac{\hbar^2}{2m} |\vec{\xi} + \vec{g}|^2 + V_0 - E(\vec{\xi}) \right) b_{\vec{g}}(\vec{\xi}) + \sum_{\vec{h}} V_{\vec{g}-\vec{h}} b_{\vec{h}}(\vec{\xi}) = 0$$

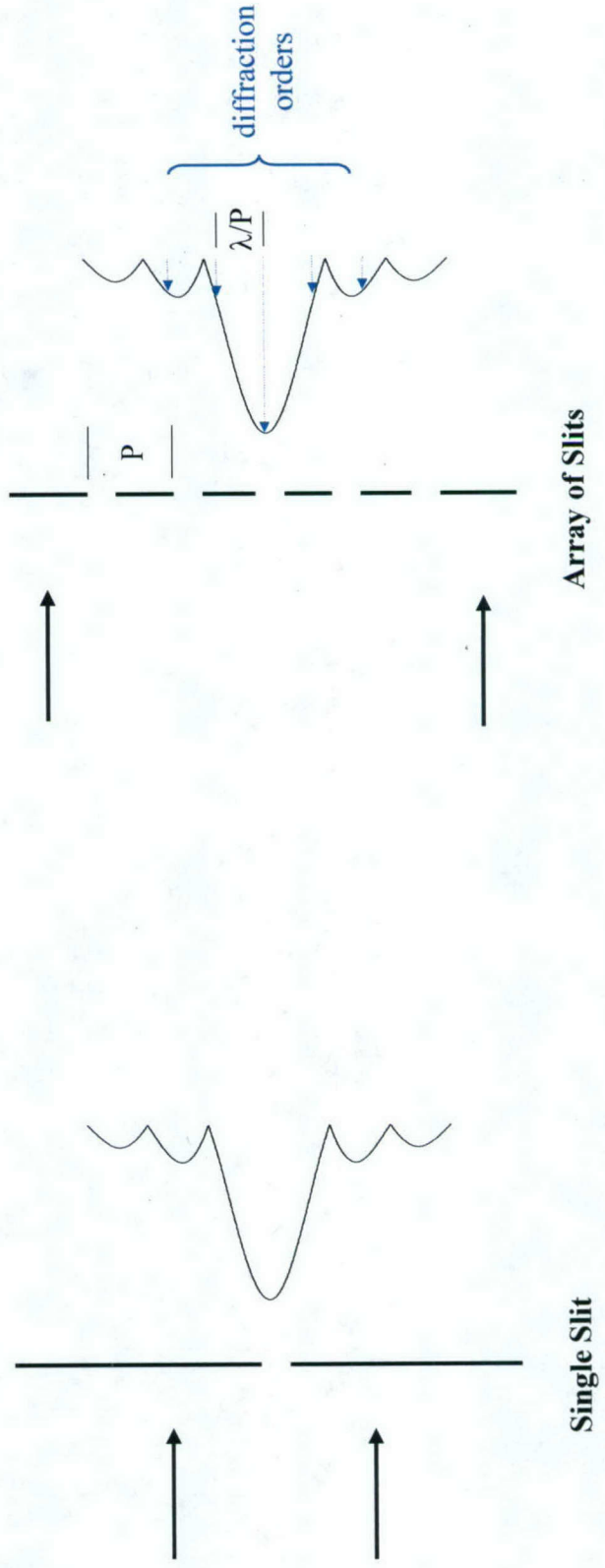
Key Point

- We do not need to know the full lattice potential:

$$\text{Fourier Transform} \{ \Omega(\vec{r}) \} \equiv V(\vec{k}) \quad - \text{Max} < k_x, k_y, k_z < \text{Max}$$

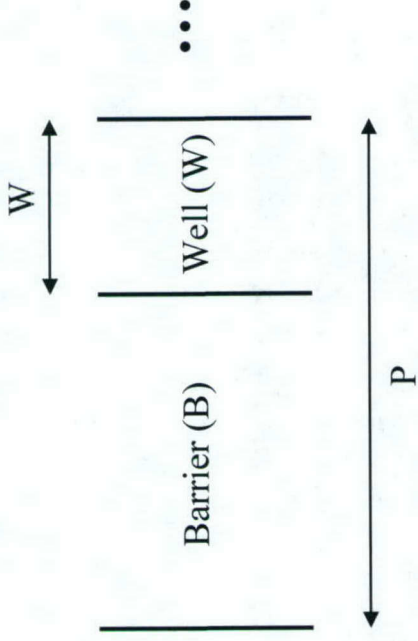
We only need $V(\vec{k} = \vec{g}) \equiv V_{\vec{g}}$ (form factors)

Optics Analogy:



How do we form V for the Superlattice ??

- There are at least two methods for representing the potential of a superlattice (W / B):



- Method (1): “Atomistic” EPM = AEPM

$$V(\vec{r}) = \sum_{\text{Sum over W-sites}} \Omega_W(\vec{r} + \vec{t}_W) + \sum_{\text{Sum over B-sites}} \Omega_B(\vec{r} + \vec{t}_B) + \text{Interface detail}$$

Key Point: This construction requires functional fits to $\Omega_W(\vec{r})$ and $\Omega_B(\vec{r})$ + others

Example: InAs / GaSb requires $\Omega_{In(As)}(\vec{r}), \Omega_{Ga(Sb)}(\vec{r}), \Omega_{Ga(As)}(\vec{r}), \Omega_{In(Sb)}(\vec{r})$

(8 ions x 5 parameters/ion + 3 offsets) = 43 parameters
guess of potential + interface bond weightings + Temp. dependent segregation

- Method (2): Superimposed “Bulk” EPM = SEPM

$$V_W(\vec{r}) = \sum_{\vec{g}} V_{\vec{g}}^W e^{i\vec{g} \cdot \vec{r}}$$

$$V_B(\vec{r}) = \sum_{\vec{g}} V_{\vec{g}}^B e^{i\vec{g} \cdot \vec{r}}$$

$$V(\vec{r}) = \text{rect}\left(\frac{z}{W}\right) \cdot V_W(\vec{r}) + \left[1 - \text{rect}\left(\frac{z}{W}\right)\right] \cdot V_B(\vec{r})$$

in which:

$$\text{rect}\left(\frac{z}{W}\right) = \sum_{n=-M}^M \frac{1}{\pi} \sin\left(\frac{\pi W}{P} \cdot n\right) e^{i \frac{2\pi}{P} z} = \text{[Diagram of a periodic square wave with period P and height W]} \dots$$

Key Point: This construction only requires $V_{\vec{g}}^W$ and $V_{\vec{g}}^B$ (finite number of form factors)

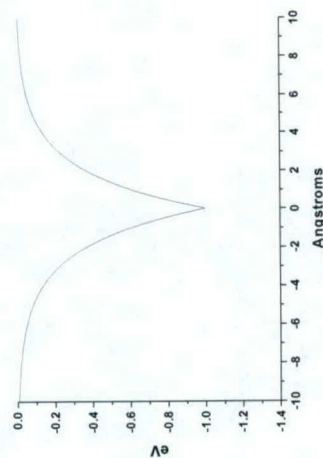
that fit the bulk band diagram plus the offset.

(8 parameters for strained InAs + 7 parameters for GaSb + offset) = 16 parameters

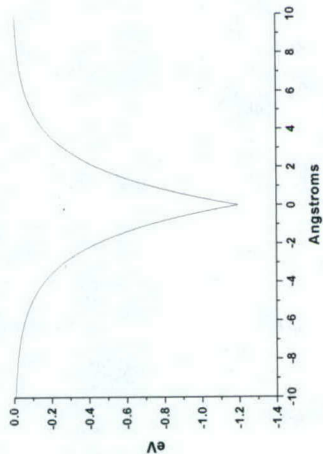
Graphical comparison in 1-dimension

(6ML / 12ML)

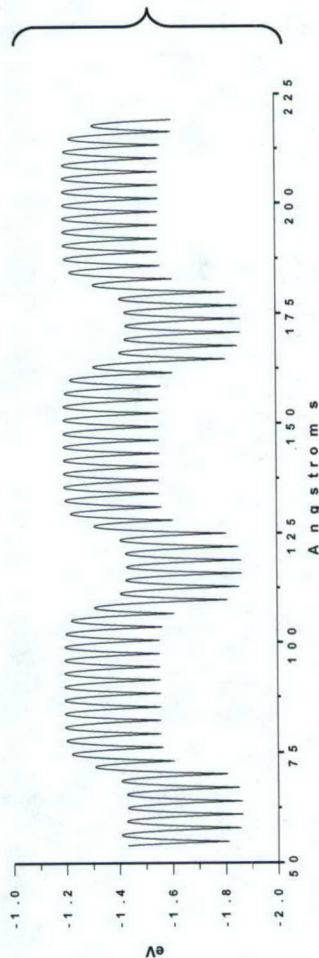
Barrier Lattice
Potential



Well Lattice
Potential



Method (1)
AEPM



Construction requires
full knowledge of
 $V_W(\vec{k})$ and $V_B(\vec{k})$ for
- $Max < \vec{k} < Max$.

Method (2)
SEPM



Construction uses finite
number of form factors,
 $V_W(\vec{g})$ and $V_B(\vec{g})$.
**Interface complexity is
covered by one
parameter: Offset**

- For both methods, the final potential can be written as a sum

$$V(\vec{r}) \equiv \sum_{\vec{g}_{\parallel}, n} \bar{V}_{\vec{g}_{\parallel}, n} e^{i(g_x x + g_y y)} e^{i \frac{2\pi n}{P} z} \quad \text{SEPM or AEPM}$$

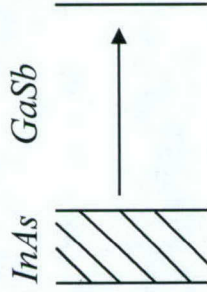
but Fourier coefficients $\bar{V}$ change.

- The Schroedinger Equation for the superlattice is:

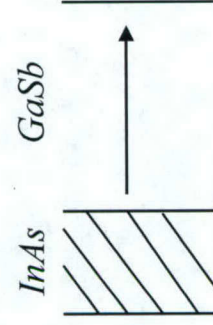
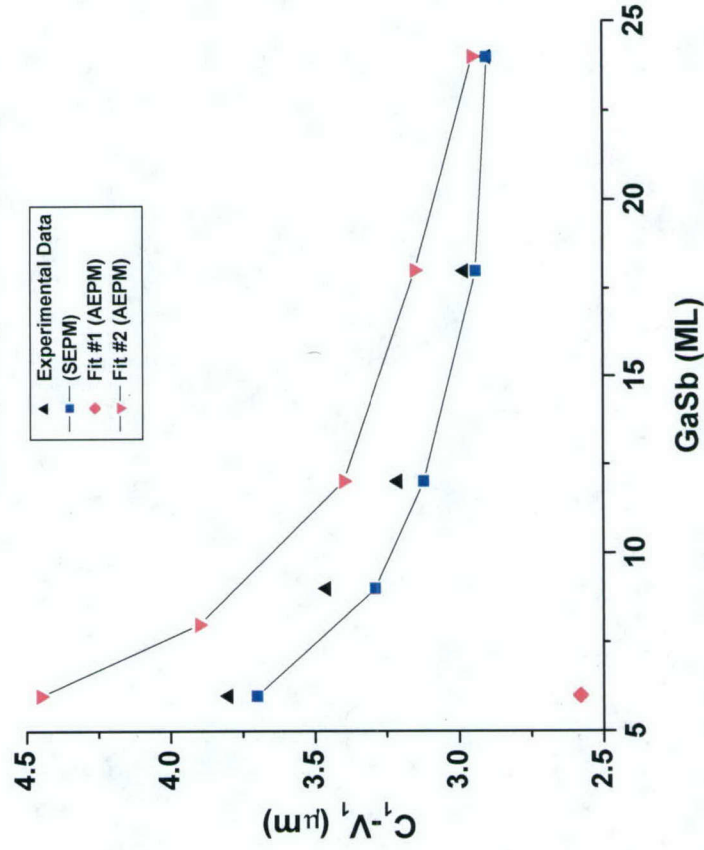
$$\frac{\hbar^2}{2m} \left[|\vec{g}_{\parallel} + \vec{\xi}_{\parallel}|^2 + \left(\frac{2\pi n}{P} + \xi_z \right)^2 \right] a_{\vec{g}_{\parallel}, n} + \sum_{\vec{g}'_{\parallel}, n'} \bar{V}_{\vec{g}_{\parallel} - \vec{g}'_{\parallel}, n - n'} a_{\vec{g}'_{\parallel}, n'} = E(\vec{\xi}) a_{\vec{g}_{\parallel}, n}$$

Question for Discussion: *Which model, SEPM or AEPM, represents reality?*

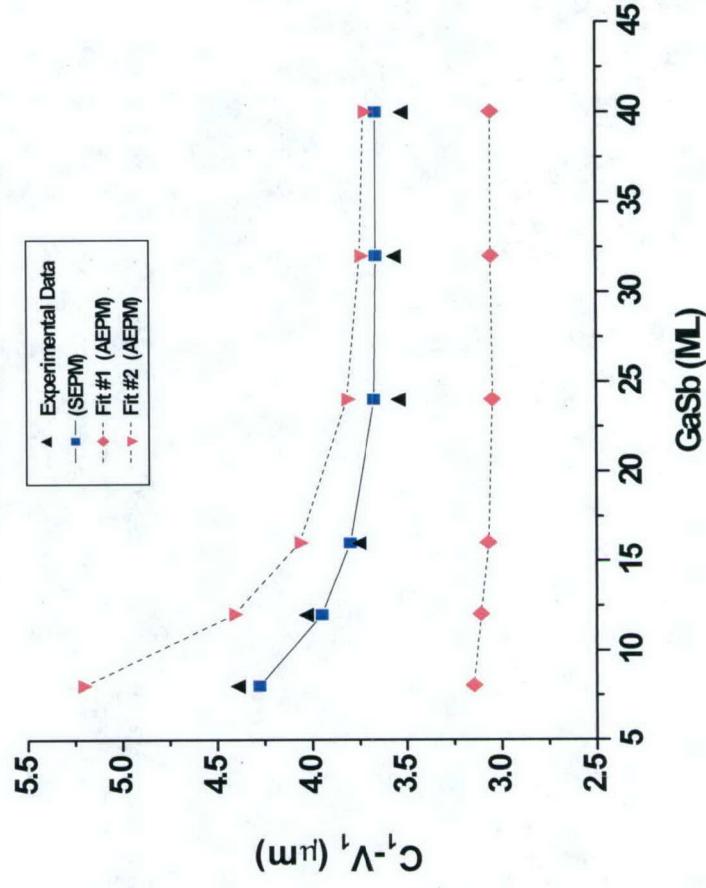
Superlattice (InAs / GaSb) Blue Shift Results -vs- GaSb Thickness



InAs (6 ML) / GaSb (x ML)



InAs (8 ML) / GaSb (x ML)



- Fit #1 and Fit #2 both provide excellent fits to the *InAs* and *GaSb* band diagrams, but they interpolate differently.

Application of SEPM to Mid-IR Laser Tuning

SEPM model calculations, assuming 24 Å of $\text{In}_{0.4}\text{Ga}_{0.6}\text{Sb}$ hole well and thick $\text{In}_{0.2}\text{Ga}_{0.8}\text{AsSb}$ internal absorbers.

